



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

MPSW56 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -500 mA

Collector-base voltage

$V_{(BR)CBO}$: -80 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92

1. EMITTER
2. BASE
3. COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-50mA$	100			
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-250mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-250mA, I_B=-10mA$			-0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5V, I_C=-250mA$			-1.2	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-250mA$		50		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		15		pF